TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

TPCA8024

Lithium-Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $RDS(ON) = 3.5 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 72 \text{ S (typ.)}$
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5 V ($V_{DS} = 10$ V, $I_{D} = 1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

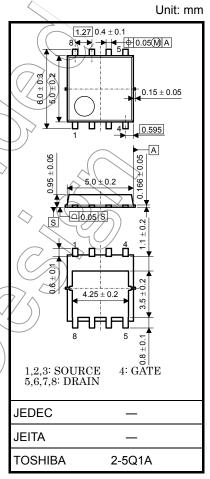
Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	30	> V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	ID <	35	A	
Drain current	Pulse (Note 1)	I _{DP}	105		
Drain power dissipation	on (Tc=25°C)	PD (35	W	
Drain power dissipation (t = 10 s) (Note 2a)		PD	2.8	w	
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	1.6	W	
Single pulse avalanch	ne energy (Note 3)	EAS	159	mJ	
Avalanche current	7,	IAR	35	Α	
Repetitive avalanche energy (17c=25°C) (Note 4)		E _{AR}	3.5	mJ	
Channel temperature		Tch	150	°C	
Storage temperature range		Tstg	-55 to 150	°C	

Note: For Note 1 to 4, refer to the next page

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor

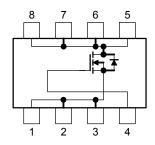
Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

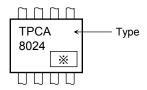
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	3.57	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

Marking (Note 5)

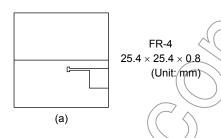


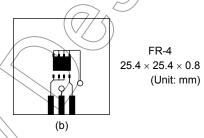
Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2:

(a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.1 mH, $R_G = 25 \Omega$, $A_R = 35 \text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel/temperature

Note 5: * Weekly code: (Three digits)

Week of manufacture
(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture

(The last digit of the year)

(The last digit of the year)

2

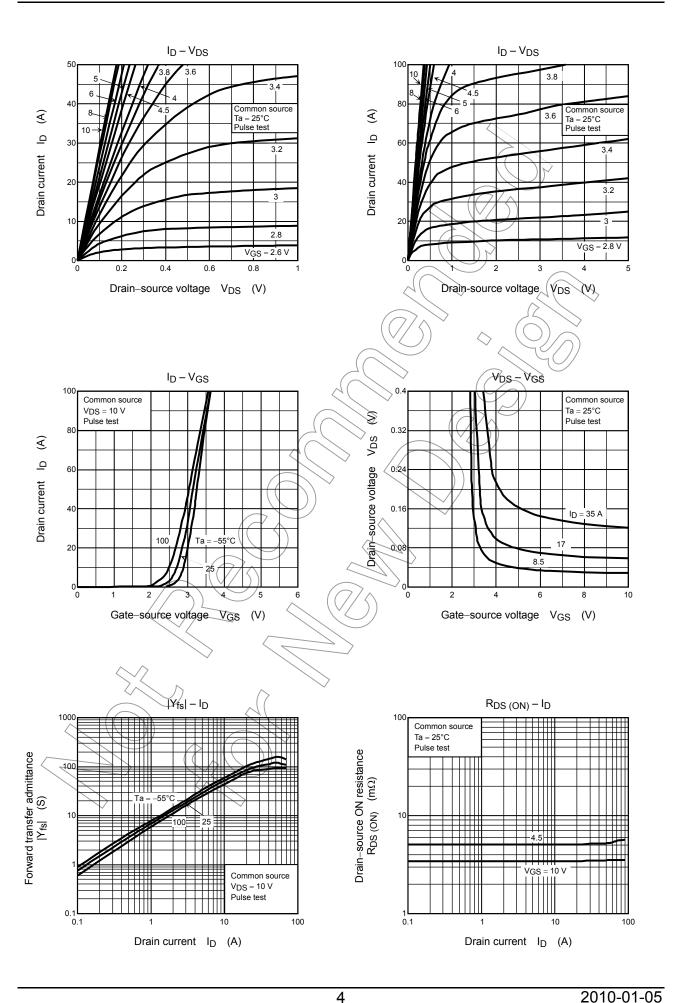
Electrical Characteristics (Ta = 25°C)

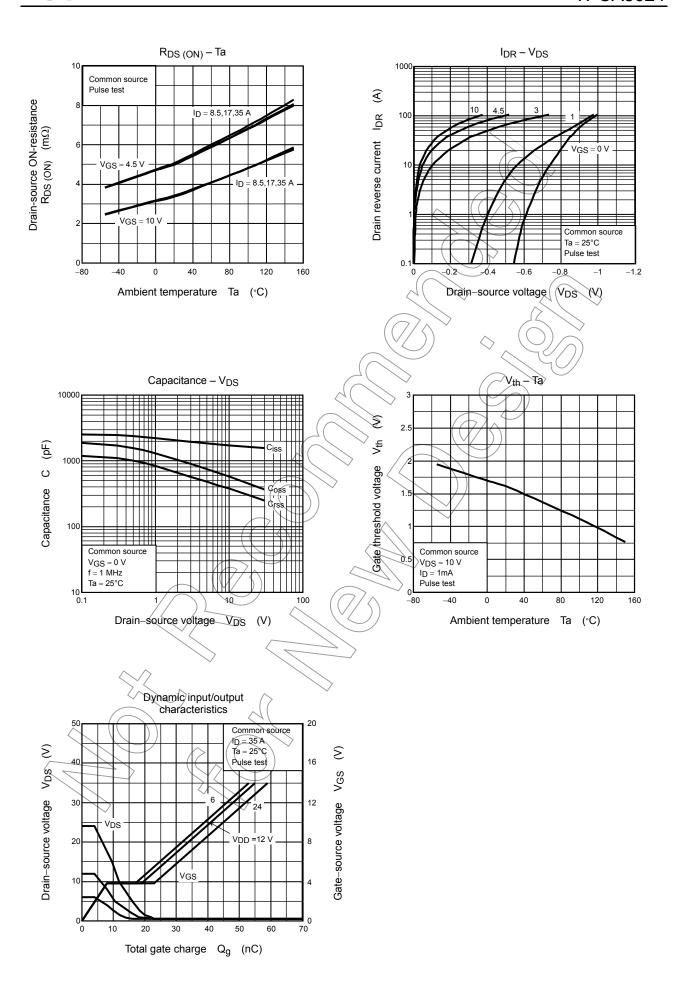
Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF cu	rrent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
		V _{(BR) DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_	v
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3) / _	2.5	V
Drain-source ON-resistance		D	V _{GS} = 4.5 V, I _D = 17 A	<u> </u>	5.4	7.8	- mΩ
		R _{DS} (ON)	V _{GS} = 10 V, I _D = 17 A))	3.5	4.3	
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 17 A	36	72	_	S
Input capacitance		C _{iss}		² —	1800	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	370	_	pF
Output capacitance		Coss			570	\rightarrow	
Switching time	Rise time	t _r	V _{GS} 10 V I _D = 17 A O V _{OUT} G 88 O O O O O O O O O O O O O O O O	-(11	> _	
	Turn-on time	t _{on}			19	_	
	Fall time	t _f	2	(\mathcal{A})	22	_	ns
	Turn-off time	t _{off}	V _{DD} = 15 V Duty ≤ 1%, t _w = 10 μs) —	64	_	
Total gate charge (gate-source plus		Qg	V _{DD} ≈ 24 V, V _{GS} = 10 V,	_	45	_	
Gate-source charge 1		Q _{gs1}	I _D = 35 A		8		nC
Gate-drain ("miller") charge		Qgd			15		

Source-Drain Ratings and Characteristics (Ta = 25°C)

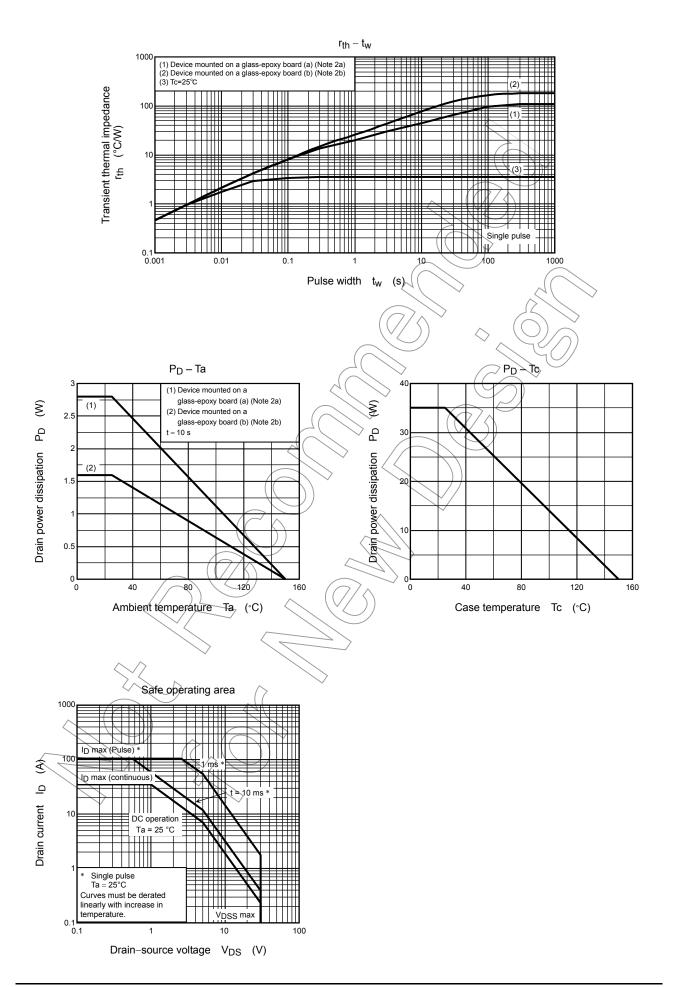
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Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note-1)	I _{DRP}	_	_	_	105	Α
Forward voltage (diode)	VDSE	$I_{DR} = 35 \text{ A}, V_{GS} = 0 \text{ V}$	_		-1.2	V







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